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Docket: AM-3245

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Date: 9 August 2001 Ingrid C. Mallory
Ingrid C. Mallory

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hoiman HUNG et al.

Attorneys Docket: AM-3245

Serial No.: 09/276,376

Art Unit No.: 1746

Filed: March 25, 1999

Examiner: A. Olsen

For: "ENHANCEMENT OF SILICON OXIDE ETCH RATE AND SUBSTRATE SELECTIVITY WITH XENON ADDITION"

Commissioner of Patents and Trademarks
Washington, DC 20231

AMENDMENT UNDER 37 CFR §1.116

Sir:

In response to the Office Action of June 14, 2000, please amend the above application as follows:

In the specification:

Paragraph at page 11, line 22 to page 12, line 4:

Two series of experiments were performed which measured oxide and nitride etch rates for blanket structures, that is, unpatterned oxide and nitride layers. The experiments used a combination of C_4F_6 and either Ar and Xe. The selectivity to nitride is plotted in FIG. 8 for the two diluent gases as a function of the diluent flows. The two diluents exhibit significantly

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